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# Octal D-Type Latch with 3-State Output

The MC74VHC573 is an advanced high speed CMOS octal latch with 3-state output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This 8-bit D-type latch is controlled by a latch enable input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed:  $t_{PD} = 4.5 \text{ ns (Typ)}$  at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 1.2 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 218 FETs or 54.5 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

## **PIN ASSIGNMENT**

OE [	1●	20	] v <sub>cc</sub>
D0 [	2	19	] Q0
D1 [	3	18	] Q1
D2 [	4	17	] Q2
D3 [	5	16	] Q3
D4 [	6	15	] Q4
D5 [	7	14	] Q5
D6 [	8	13	] Q6
D7 [	9	12	] Q7
GND [	10	11	LE
			•



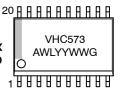
## ON Semiconductor

http://onsemi.com

## **MARKING DIAGRAMS**

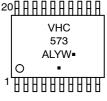


SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





SOEIAJ-20 M SUFFIX CASE 967

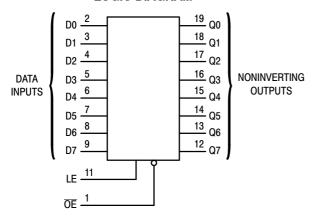
VHC573 = Specific Device Code A = Assembly Location WL. L = Wafer Lot

WL, L = Water Lot
Y = Year
WW, W = Work Week
G or ■ = Pb-Free Package
(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping
MC74VHC573DWR2G	SOIC-20	1000 / Reel
MC74VHC573DTR2G	TSSOP-20	2500 / Reel
MC74VHC573MELG	SOEIAJ-20	2000 / Reel

## **LOGIC DIAGRAM**



## **FUNCTION TABLE**

INPUTS			OUTPUT
ŌĒ	LE	D	q
L	Н	Н	Н
L	Н	L	L
L	L	Х	No Change
Н	Х	Х	Z

### **MAXIMUM RATINGS\***

Symbol	Paramete	r	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage		- 0.5 to + 7.0	V
V <sub>out</sub>	DC Output Voltage		- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input Diode Current	- 20	mA	
I <sub>OK</sub>	Output Diode Current		± 20	mA
l <sub>out</sub>	DC Output Current, per Pin		± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and G	ND Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†		500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C	

<sup>\*</sup> Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage		2.0	5.5	V
V <sub>in</sub>	DC Input Voltage		0	5.5	V
V <sub>out</sub>	DC Output Voltage	DC Output Voltage		V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature		- 40	+ 85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time V <sub>CC</sub> V <sub>CC</sub>	= 3.3V = 5.0V	0	100 20	ns/V

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{\rm in}$  and  $V_{\rm out}$  should be constrained to the

range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

## DC ELECTRICAL CHARACTERISTICS

			v <sub>cc</sub>		T <sub>A</sub> = 25°C		T <sub>A</sub> = - 40	0 to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V <sub>CC</sub> x 0.7			1.50 V <sub>CC</sub> x 0.7		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V <sub>CC</sub> x 0.3		0.50 V <sub>CC</sub> x 0.3	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		٧
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4mA$ $I_{OH} = -8mA$	3.0 4.5	2.58 3.94			2.48 3.80		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4\text{mA}$ $I_{OL} = 8\text{mA}$	3.0 4.5			0.36 0.36		0.44 0.44	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μА

<sup>†</sup>Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

### DC ELECTRICAL CHARACTERISTICS

			V <sub>cc</sub>		T <sub>A</sub> = 25°C		$T_A = -40$	) to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
l <sub>oz</sub>	Maximum Three-State Leakage Current	$V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	5.5			± 0.25		± 2.5	μА
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0	μА

## AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0$ ns)

					T <sub>A</sub> = 25°C		T <sub>A</sub> = -4	0 to 85°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, LE to Q	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		7.6 10.1	11.9 15.4	1.0 1.0	14.0 17.5	ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		5.0 6.5	7.7 9.7	1.0 1.0	9.0 11.0	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, D to Q	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		4.5 6.0	6.8 8.8	1.0 1.0	8.0 10.0	
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time, OE to Q	$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 V \\ R_L &= 1 k \Omega \end{aligned}$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		7.3 9.8	11.5 15.0	1.0 1.0	13.5 17.0	ns
		$\begin{aligned} V_{CC} &= 5.0 \pm 0.5 V \\ R_L &= 1 k \Omega \end{aligned}$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		5.2 6.7	7.7 9.7	1.0 1.0	9.0 11.0	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time, OE to Q	$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 V \\ R_L &= 1 k \Omega \end{aligned}$	C <sub>L</sub> = 50pF		10.7	14.5	1.0	16.5	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	C <sub>L</sub> = 50pF		6.7	9.7	1.0	11.0	
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output to Output Skew	V <sub>CC</sub> = 3.3 ± 0.3V (Note 1)	C <sub>L</sub> = 50pF			1.5		1.5	ns
		V <sub>CC</sub> = 5.5 ± 0.5V (Note 1)	C <sub>L</sub> = 50pF			1.0		1.0	ns
C <sub>in</sub>	Maximum Input Capacitance				4	10		10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)				6				pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
$C_{PD}$	Power Dissipation Capacitance (Note 2)	29	pF

## NOISE CHARACTERISTICS (Input $t_{\text{f}}$ = $t_{\text{f}}$ = 3.0ns, $C_{\text{L}}$ = 50 pF, $V_{CC}$ = 5.0V)

			T <sub>A</sub> = 25°C		
Symbol	Symbol Parameter		Max	Unit	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>		1.2	V	
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>		- 1.2	V	
V <sub>IHD</sub>	V <sub>IHD</sub> Minimum High Level Dynamic Input Voltage		3.5	V	
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V	

Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.
 C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/8 (per latch). C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

## **TIMING REQUIREMENTS** (Input $t_r = t_f = 3.0 \text{ns}$ )

			T <sub>A</sub> =	25°C	T <sub>A</sub> = - 40 to 85°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t <sub>w(h)</sub>	Minimum Pulse Width, LE	$V_{CC} = 3.3 \pm 0.3V$ $V_{CC} = 5.0 \pm 0.5V$		5.0 5.0	5.0 5.0	ns
t <sub>su</sub>	Minimum Setup Time, D to LE	$V_{CC} = 3.3 \pm 0.3V$ $V_{CC} = 5.0 \pm 0.5V$		3.5 3.5	3.5 3.5	ns
t <sub>h</sub>	Minimum Hold Time, D to LE	$V_{CC} = 3.3 \pm 0.3V$ $V_{CC} = 5.0 \pm 0.5V$		1.5 1.5	1.5 1.5	ns

## **SWITCHING WAVEFORMS**

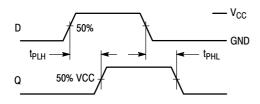


Figure 1.

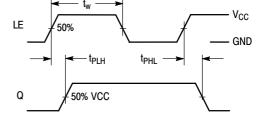


Figure 2.

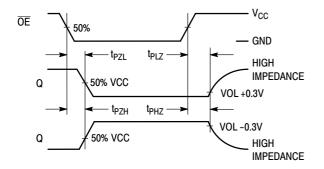


Figure 3.

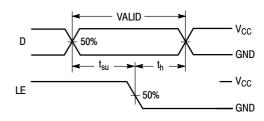
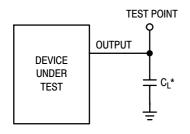
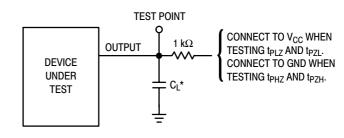


Figure 4.

## **TEST CIRCUITS**



\*Includes all probe and jig capacitance

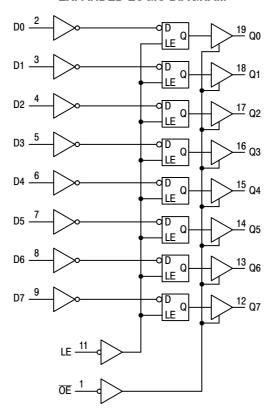


\*Includes all probe and jig capacitance

Figure 5.

Figure 6.

## **EXPANDED LOGIC DIAGRAM**



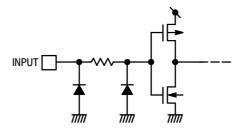
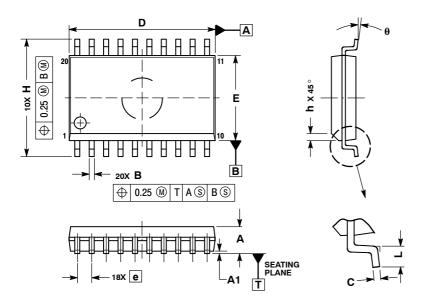


Figure 7. Input Equivalent Circuit

## **PACKAGE DIMENSIONS**

## SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**



#### NOTES:

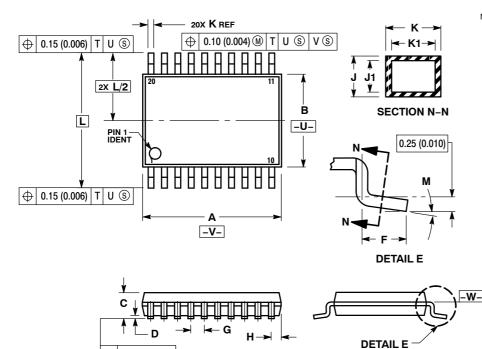
- NOTES:

  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0°	7 °			

### PACKAGE DIMENSIONS

## TSSOP-20 CASE 948E-02 ISSUE C



0.100 (0.004)

#### NOTES:

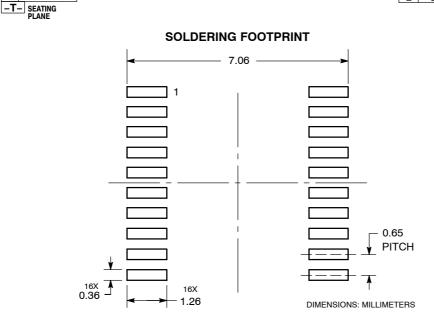
- 1. DIMENSIONING AND TOLERANCING PER

- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION:
  MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE
  MOLD FLASH, PROTRUSIONS OR GATE
  BURRS. MOLD FLASH OR GATE BURRS. SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION
- INTERLEAD FLASH OR PROTRUSION
  SHALL NOT EXCEED 0.25 (0.10) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE
  DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08
  (0.003) TOTAL IN EXCESS OF THE K
  DIMENSION AT MAXIMUM MATERIAL
  CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR
  DEFERENCE ONLY
- REFERENCE ONLY.

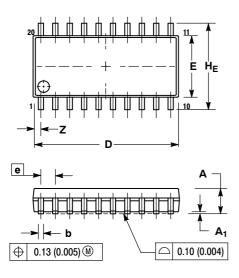
  7. DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE -W-

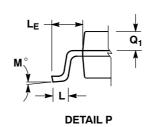
<u> JETERMINED AT DATUM PLANE -W</u>							
	MILLIMETERS		INCHES				
DIM	MIN	MAX	MIN	MAX			
Α	6.40	6.60	0.252	0.260			
В	4.30	4.50	0.169	0.177			
С	-	1.20		0.047			
D	0.05	0.15	0.002	0.006			
F	0.50	0.75	0.020	0.030			
G	0.65 BSC		0.026 BSC				
Н	0.27	0.37	0.011	0.015			
J	0.09	0.20	0.004	0.008			
J1	0.09	0.16	0.004	0.006			
K	0.19	0.30	0.007	0.012			
K1	0.19	0.25	0.007	0.010			
L	6.40 BSC		0.252 BSC				
M	0°	8°	0°	8°			

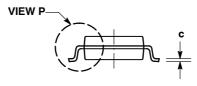


## PACKAGE DIMENSIONS

SOEIAJ-20 CASE 967-01 ISSUE A







#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
   ALA FM. 1999
- Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- 2. DIMENSIONS D AND E DO NOT INCLUDE
  MOLD FLASH OR PROTRUSIONS AND ARE
  MEASURED AT THE PARTING LINE. MOLD FLASH
  OR PROTRUSIONS SHALL NOT EXCEED 0.15
  (0.006) PER SIDE.
- (0.006) PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0°	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		0.81		0.032

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